Author Correction: Rapid gate-based spin read-out in silicon using an on-chip resonator

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In the version of this Letter originally published, the second, third and fourth exponential terms in equation (3) were incorrect; the corrected equation is shown below.

$$n_S = \frac{1}{\sqrt{2\pi}\sigma_S} e^{-\frac{(|S_{21}| - \mu_S)^2}{2\sigma_S^2}} e^{-\frac{t_{\text{int}}}{T_1}} + \frac{1}{\sqrt{2\pi}\sigma_S} \frac{t_{\text{int}}}{T_1} \int_{\mu_T \mu_S - \mu_T}^{\mu_S} \frac{1}{\mu_T \mu_S - \mu_T} e^{-\frac{x - \mu_T}{\mu_S - \mu_T} \frac{t_{\text{int}}}{T_1}} e^{-\frac{(|S_{21}| - x)^2}{2\sigma_S^2}} dx \quad (3)$$

The correct equation was used for data analysis. The online versions have been amended.

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